

34 V Input Synchronous Step-down DC / DC Controller Evaluation Board

NO.EEV-351-032A033-0500-220218

R1272S032A033-0500EV is the evaluation board for R1272 which has the below features, benefits and specifications.

OUTLINE

The R1272S is a step-down DC/DC controller which can generate an output voltage of 0.7 V to 5.3 V by driving external high- / low-side NMOSs. By the adoption of a unique current mode PWM architecture without an external current sense resistor, the R1272S can make up a stable DC/DC converter with high-efficiency even if adding low Ron MOSFETs and a low DCR inductor externally. And, by the frequency characteristics optimization with using external phase compensation capacitor, the R1272S can achieve a high-speed response to variations of input voltage and load current. The user-settable oscillation frequency is adjustable over a range of 250 kHz to 1 MHz⁽¹⁾ by external resistors, and also can be synchronized to an external clock. Output Voltage Control Methods have three operating modes: Forced PWM mode, PLL_PWM mode, and PWM/VFM Auto-switching mode. These modes are selectable according to conditions of the MODE pin. Especially, the PWM/VFM Auto-switching mode can improve efficiency under light load conditions.

The R1272S can minimize the output voltage drop caused by an input voltage drop at cranking, with reducing the operating frequency (the lowest possible limit is a quarter of the frequency) so that the off-duty is reduced. Protection functions include a current limit function, an UVLO (Under Voltage Lock Out) function, an OVP (Over Voltage Protection) function, a soft-start function, a low-inductor current shutdown function, and so on. Also, a power good function provides the status of output with using a power good (PGOOD) pin.

For EMI reduction, SSCG (Spread-Spectrum Clock Generator) for diffused oscillation frequency at the PWM operation is optionally available.

FEATURES

- Operating Voltage (Maximum Rating) 4.0 V to 34 V (36 V)
- Operating Temperature Range ………………………………………… -40°C ≤ Ta ≤ 105°C
 - (Usable in high-temperature environment)
- Start-up Voltage ------ 4.5 V
- Output Voltage 3.3 V
- Feedback Voltage Tolerance 0.64 V ± 1%
- Consumption Current at No Load (at VFM mode) ········ Τyp.15 μA
- Adjustable Oscillation Frequency------ 500 kHz
- Synchronizable Clock Frequency------ 250 kHz to 1 MHz
- Spreading Rate for SSCG Typ. ±3.6%
- Minimum On-Time ··· ···· Typ.100 ns
- At dropout, actual minimum off-time is reduced.
- Adjustable Soft-start Time⁽¹⁾ ······ Typ.500 μs
- Pre-bias Start-up

⁽¹⁾ 500 µs (Typ.) as a lower limit with using an external capacitor. Otherwise, available the tracking function through the application of an external voltage.

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- Anti-phase Clock Output
- Thermal Shutdown Function ······ Tj = 160°C (Typ.)
- Under Voltage Lockout (UVLO) Function------ Typ. 3.3 V
- Over Voltage Detection (OVD) Function FB pin voltage (V_{FB}) + 10% (Typ.)
- Detection/Release Hysteresis ······ FB pin voltage (V_{FB}) x 3% (Typ.)
- Under Voltage Detection (UVD) Function \cdots FB pin voltage (V_{FB}) 10% (Typ.)
- Detection/Release Hysteresis ······ FB pin voltage (V_{FB}) x 3% (Typ.)
- Over-current Protection ------- Hiccup-mode / Latch mode
- Selectable Current Limit Threshold ······· 70 mV
- Power Good Output ······ NMOS Open-drain Output
- Package ······ HSOP-18
- For more details on R1272 IC, please refer to https://www.nisshinbo-microdevices.co.jp/en/pdf/datasheet/r1272-ea.pdf.

PART NUMBER INFORMATION

Product Name	Package
R1272S032A033-0500	HSOP-18

03: Combination of processing and function.

Over Current Protection	SSCG
Latch mode	Enable

2: 70 mV, Set Voltage for Current Limit Threshold (Typ.)

A: Fixed

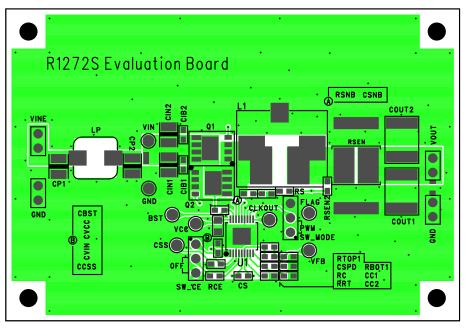
033: 3.3 V, Output Voltage

0500: 500 kHz, Frequency

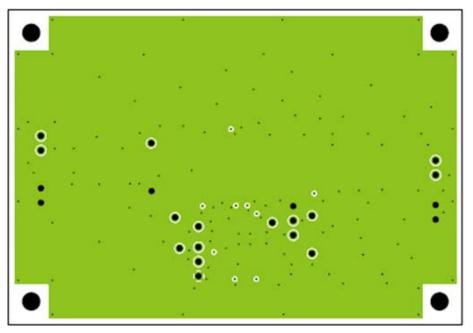
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PCB LAYOUT

R1272SxxxA PCB Layouts



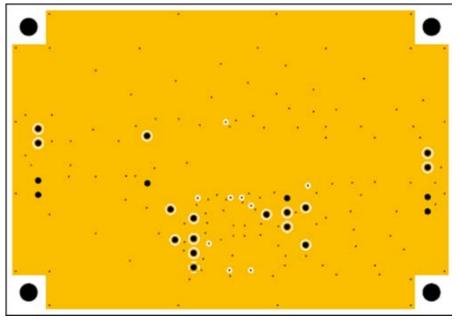
PCB Layout - 1st Layer (Top Layer)



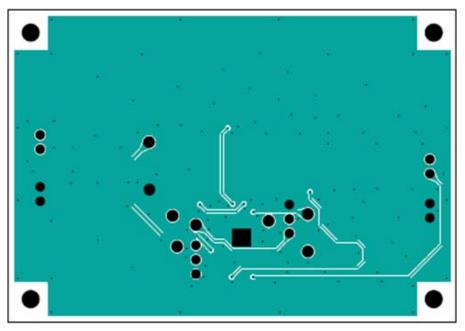
PCB Layout - 2nd Layer

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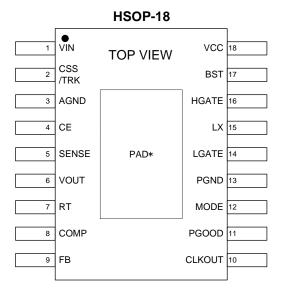
PCB Layout - 3rd Layer



PCB Layout - 4th Layer (Bottom Layer) R1272SxxxA

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PIN DESCRIPTIONS



HSOP-18 Pin Description

Pin No.	Pin Name	Description
1	VIN	Power supply pin
2	CSS/TRK	Soft-start adjustment pin
3	AGND	Analog GND pin
4	CE	Chip enable pin (Active "H")
5	SENSE	Sense pin for inductor current
6	VOUT	Output voltage feedback input pin
7	RT	Oscillation adjustment pin
8	COMP	Capacitor connecting pin for phase compensation of error amplifie
9	FB	Feedback input pin to the error amplifier
10	CLKOUT	Clock output pin
11	PGOOD	Power-good output pin
12	MODE	Mode-set input pin
13	PGND	Power GND pin
14	LGATE	L-side FET control pin
15	LX	Switchingpin
16	HGATE	H-side FET control pin
17	BST	Boostrap pin
18	VCC	VCC output pin

* The tab on the bottom of the package must be electrically connected to GND (substrate level) when mounted on the board.

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Symbol	Item	Rating	Unit	
Vin	VIN pin voltage	-0.3 to 36	V	
VCE	CE pin voltage	-0.3 to 36	V	
Vcss/Vtrk	CSS/TRK pin voltage	-0.3 to 3	V	
Vout	VOUTpin voltage	-0.3 to 6	V	
Vsense	SENSEpin voltage	-0.3 to 6	V	
V _{RT}	RT pin voltage	-0.3 to 3	V	
VCOMP	COMP pin voltage ⁽¹⁾	-0.3 to 6	V	
Vfb	FB pin voltage	-0.3 to 3	V	
Vcc	VCC pin voltage	-0.3 to 6	V	
VCC	Output current for VCC pin	Internally limited	mA	
VBST	BST pin voltage	LX-0.3 to LX+6	V	
Vhgate	HGATE pin voltage	LX-0.3 to BST	V	
V _{LX}	LX pin voltage ⁽²⁾	-0.3 to 36	V	
Vlgate	LGATE pin voltage ⁽¹⁾	-0.3 to 6	V	
VMODE	MODE pin voltage	-0.3 to 6	V	
Vpgood	PGOOD pin voltage	-0.3 to 6	V	
VCLKOUT	CLKOUT pin voltage ⁽¹⁾	-0.3 to 6	V	
PD	Power Dissipation ⁽³⁾ (HSOP-18, JEDEC STD.51-7 Test Land Pattern)	3100	mW	
Tj	Junction Temperature	-40 to 125	°C	
Tstg	Storage Temperature Range	-55 to 125	°C	

ABSOLUTE MAXIMUM RATINGS

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause permanent damage and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings are not assured.

RECOMMENDED OPERATING CONDITIONS

Symbol	ltem	Rating	Unit
Vin	Input Voltage	4.0 to 34	V
Та	Operating Temperature Range	-40 to 105	°C
Vout	Output Voltage Range	0.7 to 5.3	V

RECOMMENDED OPERATING CONDITIONS

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if they are used over such ratings by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

 $^{(1)}$ The pin voltage must be prevented from exceeding Vcc +0.3V.

 $^{(2)}$ The pin voltage must be prevented from exceeding V_{IN} +0.3V.

⁽³⁾ Refer to *POWER DISSIPATION* for detailed information.

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ELECTRICAL CHARACTERISTICS

 V_{IN} = 12 V, CE = V_{IN} , unless otherwise specified.

The specifications surrounded by are guaranteed by design engineering at $-40^{\circ}C \le Ta \le 105^{\circ}C$.

1272Sxxx		• • •		_	· ·	25°C
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
Vstart	Start-up Voltage				4.5	V
Vcc	VCC Pin Voltage (VCC–AGI	ND) VFB = 0.672 V	4.9	5.1	5.3	V
ISTANDBY	Standby Current	$V_{IN} = 34 V, CE = 0 V$		3	20	μA
I _{VIN1}	VIN Consumption Current 1 at Switching Stop in PWM mode	V _{FB} = 0.672 V, MODE = 5 V, V _{OUT} = SENSE = LX = 5 V	,	1.0	1.3	mA
Ivin2	VIN Consumption Current 2 at Switching Stop in VFM mode	X V _{FB} = 0.672 V, MODE = 0 V V _{OUT} = SENSE = LX = 5 V		15	75	μA
V _{UVLO2}		V _{cc} Rising	3.85	4.0	4.2	V
V _{UVLO1}	UVLO Threshold Voltage	V _{cc} Falling	3.1	3.3	3.4	V
		Ta = 25°C	0.6336	0.04	0.6464	
V_{FB}	FB Voltage Accuracy	-40°C ≤ Ta ≤ 105°C	0.6272	0.64	0.6528	V
fosco	Oscillation Frequency 0	RT = 135 kΩ	225	250	275	kHz
fosc1	Oscillation Frequency 1	RT = 32 kΩ	900	1000	1100	kHz
t _{OFF}	Minimum OFF Time	$V_{IN} = 5 V, V_{OUT} = 5 V$		120	190	ns
t _{ON}	Minimum ON Time			100	120	ns
fsync	Synchronizing Frequency	fosc as the reference	fosc×0.5 250		fosc×1.5	kHz
tss1	Soft-start Time 1	CSS / TRK = OPEN	0.4		0.75	ms
tss2	Soft-start Time 2	Css = 4.7 nF	1.4		2.0	ms
ITSS	Charge Current for Soft-s Pin	tart CSS / TRK = 0 V	1.8	2	2.2	μA
Vssend	CSS/TRK Pin Voltage at End Soft-start		Vfb	V _{FB} +0.03	V _{FB} +0.06	V
Rdis_css	Discharge Resistance for CSS/TRK Pin	V _{IN} = 4.5 V, CE = 0 V, CSS / TRK = 3 V	2.0	3.0	5.0	kΩ
RUPHGATE	On-resistance of Pull-up Transistor (HGATE Pin)	(BST – LX) = 5 V, I _{HGATE} = -100 mA		2.5	5.0	Ω

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 $V_{IN} = 12 \text{ V}, \text{CE} = V_{IN}, \text{ unless otherwise specified.}$ The specifications surrounded by are guaranteed by design engineering at -40°C ≤ Ta ≤ 105°C.

Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
RDOWNHGATE	On-resistance of Pull-down Transistor (HGATE Pin)	(BST – LX) = 5 V, I _{HGATE} = 100 mA		1.5	3.5	Ω
RUPLGATE	On-resistance of Pull-up Transistor (LGATE Pin)	(VCC - PGND) = 5 V, I _{LGATE} = -100 mA		4.0	7.0	Ω
Rdownlgate	On-resistance of Pull-down Transistor (LGATE Pin)	(VCC - PGND) = 5 V, I _{LGATE} = 100 mA		1.5	3.5	Ω
	Current Limit Threshold		40	50	60	mV
VILIMIT	Voltage		60	70	80	mV
	(SENSE – VOUT)		90	100	110	mV
	Reverse Current Sense		-35	-25	-15	mV
VIREVLIMIT	Threshold	MODE = H / CLK	-45	-35	-25	mV
	(SENSE – VOUT)		-60	-50	-40	mV
VLXSHORTL	LX Shot to GND Detector Threshold Voltage (VIN – LX)		0.345	0.43	0.520	V
VLXSHORTH	LX Short to VCC Detector Threshold Voltage (LX – PGND)		0.330	0.43	0.515	V
V _{CEH}	CE "High" Input Voltage		1.27			V
V _{CEL}	CE "Low" Input Voltage				1.14	V
I _{CEH}	CE "High" Input Current	CE = 34 V	0.20		2.45	μA
ICEL	CE "Low" Input Current	CE = 0 V	-1.00	0	1.00	μA
I _{FBH}	FB "High" Input Current	V _{FB} = 3 V	-0.10		0.10	μA
I _{FBL}	FB "Low" Input Current	$V_{FB} = 0 V$	-0.10		0.10	μA
V _{MODEH}	MODE "High" Input Voltage		1.33			V
VMODEL	MODE "Low" Input Voltage				0.74	V
IMODEH	MODE "High" Input Current	MODE = 6 V	1.00		6.60	μA
MODEL	MODE "Low" Input Current	MODE = 0 V	-1.00	0	1.00	μA
Vclkouth	CLKOUT Pin "High" Output Voltage	CLKOUT = Hi-z	4.7		Vcc	V
Vclkoutl	CLKOUT Pin "Low" Output Voltage	CLKOUT = Hi-z	Ō		0.1	V
T _{TSD}	Thermal Shutdown	Ta Rising	150	160		°C
T _{TSR}	Threshold Temperature	Ta Falling	125	140	1	°C

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R1272SxxxA Continued

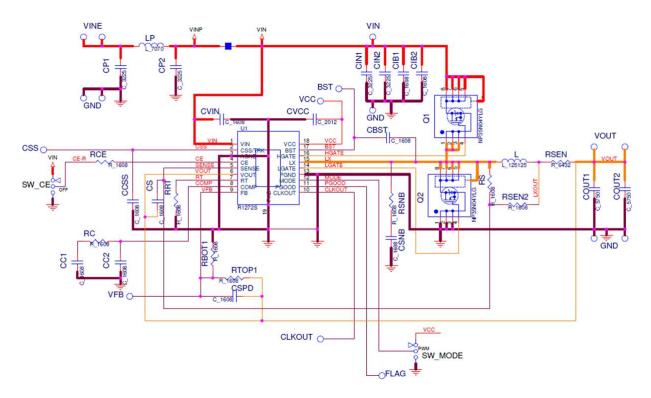
(Ta = 25°C)

Тур	Max.	Unit			
0.26	0.54	V			
0	0.10	μA			
Vfb×1.10	0.740	V			
Vfb×1.07	0.712	V			
Vfb×0.90	0.604	V			
V _{FB} ×0.93	0.628	V			
1	1.55	mS			
_	V _{FB} ×1.07 V _{FB} ×0.90	VFB×1.07 0.712 VFB×0.90 0.604 VFB×0.93 0.628			

All test items listed under Electrical Characteristics are done under the pulse load condition (Tj \approx Ta = 25°C).

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APPLICATION INFORMAITON



R1272SxxxA Typical Application Circuit at 500 kHz

CΡ1 [μF]	LP [µH]	CP2 [µF]	Q1(FET)	Q2(FET)	L [µH]	CIN1 [µF]	CIN2 [µF]
10	1.0	10	—	—	2.2	10	10
CVIN	COUT 1 [µF]	COUT2 [µF]	CBST [µF]	CVCC [µF]	CCSS [nF]	CSPD [pF]	CC1 [nF]
OPEN	100	22*2	0.22	2.2	3.3	100	6.8
CC2 [pF]	RTOP1 [kΩ]	RBOT1 [kΩ]	RC [kΩ]	RRT [kΩ]	RS	RSEN [mΩ]	RSEN2 [kΩ]
47	91.43	22	12	68	OPEN	3	1
RCE [Ω]							

R1272S032A033-0500 Recommended External Components⁽¹⁾

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⁽¹⁾ The bill of materials will be attached on the shipment of each purchased evaluation board.

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TECHNICAL NOTES

The performance of power source circuits using this IC largely depends on peripheral circuits. When selecting the peripheral components, please consider the conditions of use. Do not allow each component, PCB pattern or the IC to exceed their respected rated values (voltage, current, and power) when designing the peripheral circuits.

- External components must be connected as close as possible to the Ics and make wiring as short as possible. Especially, the capacitor connected in between VIN pin and GND pin must be wiring the shortest. If their impedance is high, internal voltage of the IC may shift by the switching current, and the operating may be unstable. Make the power supply and GND lines sufficient.
- Place a capacitor (C_{OUT}) to keep a distance between C_{IN} and C_{OUT} in order to avoid the high-frequency noise by input.
- AGND and PGND for the controller must be wired to the GND line at the low impedance point of the same layer with C_{IN} and C_{OUT}.
- Place a capacitor (C_{BST}) as close as possible to the LX pin and the BST pin. If controlling slew rate for EMI, a resistor (R_{BST}) should be in series between the BST pin and the capacitor (C_{BST}), but not be in series to FET for HGATE and LGATE pins. Because connecting the resistor in series to the FET becomes a cause of a through-current.
- The tab on the bottom of the HSOP-18 package must be connected to GND when mounted on the board. To improve thermal dissipation on the multilayer board, set via to release the heat to the other layer in the connecting part of the tab on the bottom. Likewise, thermal dissipation for FET is required.
- The MODE pin requires the H / L voltages with the high stability when the forced PWM mode (MODE = "H") or the VFM mode (MODE = "L") is enabled. If the voltage with the high stability cannot be applied, connection to the VCC pin as "H" level or the AGND pin as "L" level is recommended. If connecting to the PGND pin as noisy, a malfunction may occur. Avoid the use of the MODE pin being "Open".
- If VOUT is a minus potential, the setup cannot occur.
- The power for the controller and for the high-side FET must be used on the same power supply, since the internal slope compensation is applied as the power supply voltage of the high-side FET is equal to the controller's. If applying the other power supply voltage, the controller will become unstable owing to the inappropriate slope compensation.

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